

L Number	Hits	Search Text	DB	Time stamp
1	0	(variable adj resistane adj material) and memory and source and drain	USPAT	2004/08/25 09:37
2	3	(variable adj resistance adj material) and memory and source and drain	USPAT	2004/08/25 09:39
3	4	(variable adj resistance adj material) and memory and source and drain	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 09:44
4	182	(variable adj resistance) and memory and source and drain	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 09:53
5	552	(variable adj resistance) and memory and source and drain	USPAT	2004/08/25 10:22
6	139	source and drain and chalcogenide	USPAT	2004/08/25 10:31
7	98	source and drain and chalcogenide	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:51
8	9	pcram and memory	USPAT	2004/08/25 10:54
9	69	pcram and memory	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:54

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